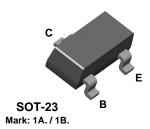
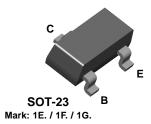


BC846A BC846B

BC847A BC847B BC847C





NPN General Purpose Amplifier

This device is designed for low noise, high gain, general purpose amplifier applications at collector currents from 1.0 μA to 50 mA. Sourced from Process 07.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter		Value	Units
V _{CEO}	Collector-Emitter Voltage	BC846 series BC847 series	65 45	V V
V _{CES}	Collector-Base Voltage	BC846 series BC847 series	80 50	V V
V_{EBO}	Emitter-Base Voltage		6.0	V
Ic	Collector Current - Continuous		100	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range		-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BC846 / BC847	
P _D	Total Device Dissipation	325	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

^{*}Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

(continued)

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TA = 25°C unless otherwise noted

Symbol	Parameter	Test Condit	ions	Min	Max	Units
OFF CHAP	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown	$I_C = 10 \text{ mA}, I_B = 0$	846A / B	65		V
	Voltage		847A / B	45		
V _{(BR)CES}	Collector-Base Breakdown Voltage	$I_C = 10 \mu A, I_E = 0$	846A / B	80		V
			847A / B	50		
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$		6.0		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}$			15	nA
		$V_{CB} = 30 \text{ V}, T_A = 150^{\circ}\text{C}$			5.0	μΑ

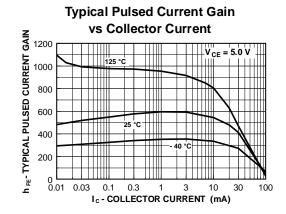
ON CHARACTERISTICS

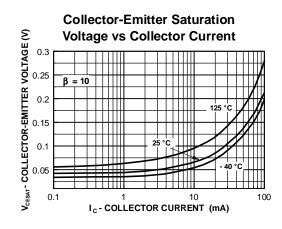
h _{FE}	DC Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$			
		846A / 847A	110	220	
		846B / 847B	200	450	
		847C	420	800	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$		0.25	V
		$I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$		0.6	V
V _{BE(on)}	Base-Emitter On Voltage	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	0.58	0.70	V
		$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$		0.77	V

SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 5.0,$ f = 100 MHz	100		MHz
C _{obo}	Output Capacitance	V _{CB} = 10 V, f = 1.0 MHz		4.5	pF
NF	Noise Figure	$I_C = 0.2 \text{ mA}, V_{CE} = 5.0,$ $R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz},$ BW = 200 Hz		10	dB

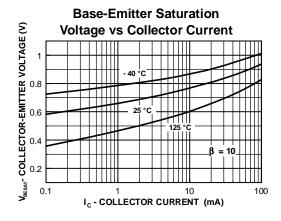
Typical Characteristics

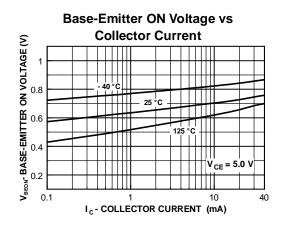




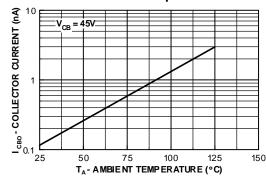
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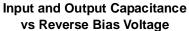
Typical Characteristics

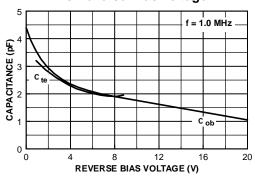




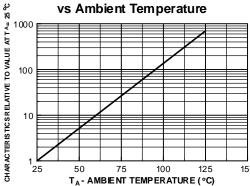
Collector-Cutoff Current vs Ambient Temperature



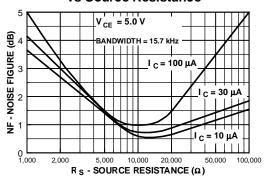




Normalized Collect or-Cutoff Current vs Ambient Temperature

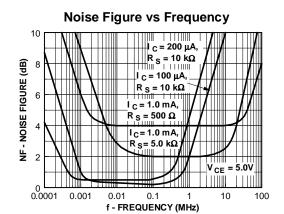


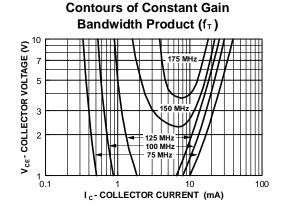
Wideband Noise Frequency vs Source Resistance

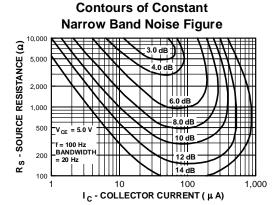


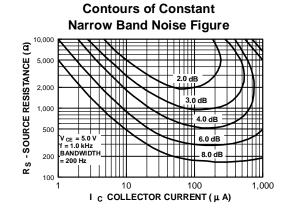
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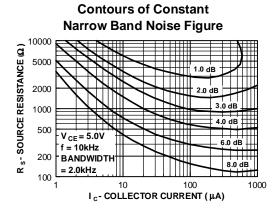
Typical Characteristics (continued)

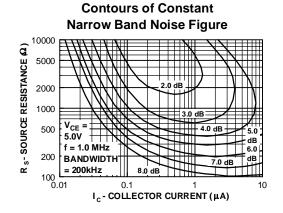








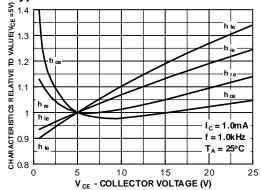




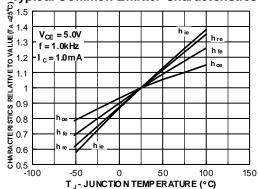
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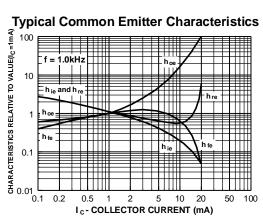
Typical Common Emitter Characteristics (f = 1.0 kHz)





Typical Common Emitter Characteristics





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